

DSS5160FDB

#### 60V DUAL PNP LOW VCE(sat) TRANSISTOR

#### **Features**

- BV<sub>CEO</sub> > -60V
- I<sub>C</sub> = -1A high Continuous Collector Current
- $R_{CE(sat)} = 200 m\Omega$  for a Low Equivalent On-Resistance
- Low Saturation Voltage V<sub>CE(sat)</sub> < 340mV @ 1A</li>
- P<sub>D</sub> up to 2.47W for power demanding applications
- R<sub>θJA</sub> efficient, 40% lower than SOT26
- Low profile 0.6mm high package for thin applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

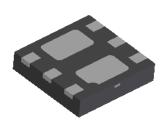
#### **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208@4)
- Weight: 0.0065 grams (Approximate)

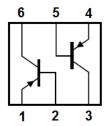
## **Application**

- Load Switch
- Power Management
- Charging Circuits
- Power Switches (e.g. Motors, Fans)

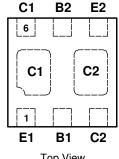
#### U-DFN2020-6



Bottom View



Device Symbol



Top View Pin-Out

### Ordering Information (Notes 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS5160FDB-7	2A	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



2A = Product type Marking Code

Y = Year: 0~9

W = Week:  $A \sim Z$ :  $1 \sim 26$  week;  $a \sim z$ ;  $27 \sim 52$  week; z represents

52 and 53 week  $X = A \sim Z$ : Internal code



## Absolute Maximum Ratings - Q1 & Q2 (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-60	V
Collector-Emitter Voltage	$V_{\sf CEO}$	-60	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	I <sub>C</sub>	-1	A
Peak Pulse Collector Current	I <sub>CM</sub>	-1.5	Α
Base Current	I <sub>B</sub>	-300	mA
Peak Base Current	I <sub>BM</sub>	-1	Α

# Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Notes 5 & 7)		405	mW	
Power Dissipation	(Notes 5 & 8)	п	510		
Power Dissipation	(Notes 6 & 7)	$P_{D}$	1650		
	(Notes 6 & 8)		2470		
	(Notes 5 & 7)		308		
Thermal Decistores, Junction to Ambient	(Notes 5 & 8)	П	245	°C/W	
Thermal Resistance, Junction to Ambient	(Notes 6 & 7)	$R_{\theta JA}$	76	- C/VV	
	(Notes 6 & 8)		51	1	
Thermal Resistance, Junction to Lead	(Note 9)	$R_{\theta JL}$	18	°C/W	
Operating and Storage Temperature Range		$T_{J}, T_{STG}$	-55 to +150	°C	

### ESD Ratings (Note 10)

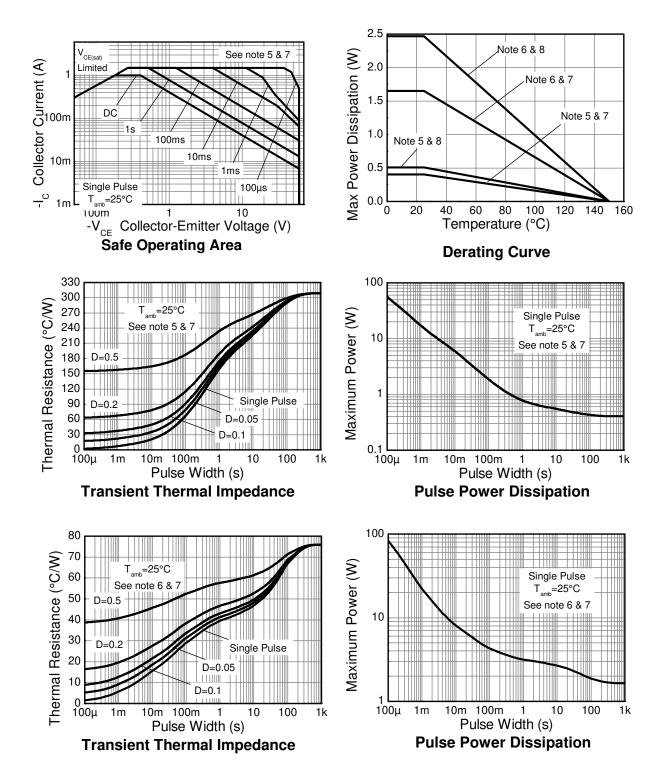
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted with the collector pad on 28mm x 28mm (8cm²) 2oz copper.
- 7. For a dual device with one active die.
- 8. For dual device with 2 active die running at equal power.
- 9. Thermal resistance from junction to solder-point (on the exposed collector pads).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



### **Thermal Characteristics and Derating Information**





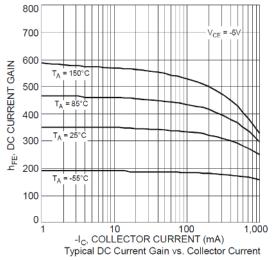
# Electrical Characteristics – Q1 & Q2 (@T<sub>A</sub> = +25°C, unless otherwise specified.)

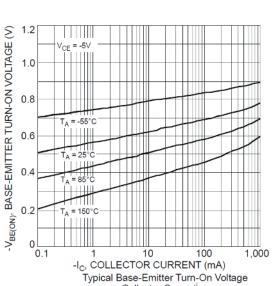
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-60			V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage (Note 11)	$BV_{CEO}$	-60	_	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7			V	$I_E = -100\mu A$
Collector-Base Cutoff Current	1	_		-100	nA	$V_{CB} = -48V, I_{E} = 0$
	I <sub>CBO</sub>	_		-50	μΑ	$V_{CB} = -48V$ , $I_E = 0$ , $T_A = +150$ °C
Emitter-Base Cutoff Current	I <sub>EBO</sub>	_		-100	nA	$V_{EB} = -5.6V, I_{C} = 0$
		170				$V_{CE} = -2V, I_{C} = -100mA$
DC Current Gain (Note 11)	h <sub>FE</sub>	120			_	$V_{CE} = -2V, I_{C} = -500mA$
		70				$V_{CE} = -2V$ , $I_C = -1A$
		_		-180		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Collector-Emitter Saturation Voltage (Note 11)	V <sub>CE(sat)</sub>	_		-340	mV	$I_C = -1A$ , $I_B = -100mA$
	02(001)	_	_	-550		$I_C = -1A$ , $I_B = -50mA$
Equivalent On-Resistance (Note 11)	R <sub>CE(sat)</sub>	_		360	mΩ	$I_E = -0.5A$ , $I_B = -50mA$
		_		-1		$I_C = -0.5A$ , $I_B = -50mA$
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	_	_	-1.0		$I_C = -1A$ , $I_B = -50mA$
		_	_	-1.1		$I_C = -1A$ , $I_B = -100mA$
Base-Emitter Turn-on Voltage (Note 11)	V <sub>BE(on)</sub>	_	_	-0.9	V	$V_{CE} = -2V, I_{C} = -0.5A$
Transition Frequency	f <sub>T</sub>	65		_	MHz	$V_{CE} = -10V, I_{C} = -50mA,$ f = 100MHz
Output Capacitance	C <sub>obo</sub>	_		15	рF	$V_{CB} = -10V$ , $f = 1MHz$
Turn-On Time	t <sub>on</sub>	_	75	_	ns	
Delay Time	t <sub>d</sub>	_	35	_	ns	
Rise Time	t <sub>r</sub>	_	40	_	ns	$V_{CC} = -10V$ , $I_{C} = -0.5A$ ,
Turn-Off Time	t <sub>off</sub>	_	265	_	ns	$I_{B1} = -I_{B2} = 25\text{mA}$
Storage Time	ts	_	230	_	ns	
Fall Time	t <sub>f</sub>		35		ns	

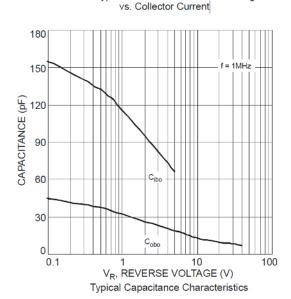
Note: 11. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s$ . Duty cycle  $\leq 2\%$ .

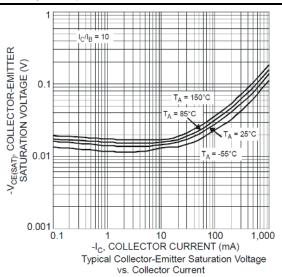


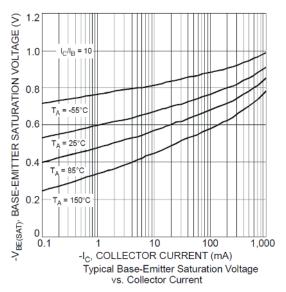
# Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







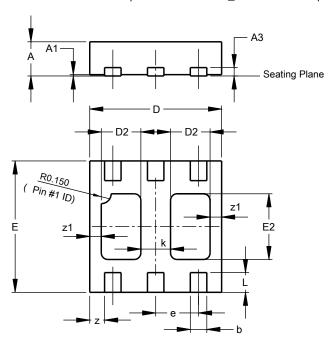






# **Package Outline Dimensions**

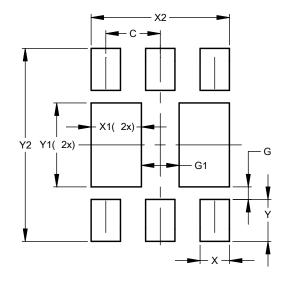
Please see AP02001 at http://www.diodes.com/\_files/datasheets/ap02001.pdf for the latest version.



U-DFN2020-6 Type B					
Dim	Min	Max	Тур		
Α	0.545	0.605	0.575		
A1	0.00	0.05	0.02		
A3	-	-	0.13		
b	0.20	0.30	0.25		
D	1.95	2.075	2.00		
D2	0.50	0.70	0.60		
е	-	-	0.65		
Е	1.95	2.075	2.00		
E2	0.90	1.10	1.00		
k	-	-	0.45		
L	0.25	0.35	0.30		
Z	-	-	0.225		
z1	-	-	0.175		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/\_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value		
Dilliensions	(in mm)		
С	0.650		
G	0.150		
G1	0.450		
X	0.350		
X1	0.600		
X2	1.650		
Y	0.500		
Y1	1.000		
Y2	2.300		



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